

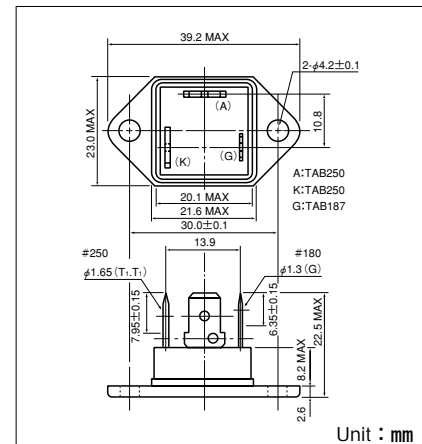
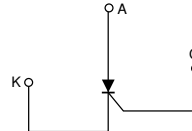
THYRISTOR MODULE (ISOLATED MOLD TYPE)

SG25AA

UL:E76102(M)

SG25AA is an isolated molded thyristor which is suitable for a wide range of industrial and home electronics uses. SG25AA uses highly reliable glass passivation.

- $I_{T(AV)}=25A$
- high Surge Capability
- Tab terminals for easy wiring.



Unit : mm

Maximum Ratings

Symbol	Item	Ratings			Unit
		SG25AA20	SG25AA40	SG25AA60	
V_{RRM}	Repetitive Peak Reverse Voltage	200	400	600	V
V_{RSM}	Non-Repetitive Peak Reverse Voltage	240	480	720	V
V_{DRM}	Repetitive Peak Off-State Voltage	200	400	600	V

Symbol	Item	Conditions	Ratings	Unit
$I_{T(AV)}$	Average On-State Current	Single phase, half wave, 180° conduction, $T_c : 70^\circ C$	25	A
$I_{T(RMS)}$	R.M.S. On-State Current	Single phase, half wave, 180° conduction, $T_c : 70^\circ C$	39	A
I_{TSM}	Surge On-State Current	$\frac{1}{2}$ cycle, 50Hz/60Hz, peak value, non-repetitive	450/500	A
I^2t	I^2t	2~10ms	1040	A ² S
PGM	Peak Gate Power Dissipation		10	W
$P_{G(AV)}$	Average Gate Power Dissipation		1	W
I_{FGM}	Peak Gate Current		3	A
V_{FGM}	Peak Gate Voltage(Forward)		10	V
V_{RGM}	Peak Gate Voltage(Reverse)		5	V
di/dt	Critical Rate of Rise of On-State Current	$I_G=100mA, T_j=25^\circ C, V_D=\frac{1}{2}V_{DRM}, dl_G/dt=1A/\mu s$	100	A/ μs
V_{iso}	Isolation Breakdown Voltage (R.M.S.)	A.C. 1 minute	2500	V
T_j	Operating Junction Temperature		-40 to +125	°C
T_{stg}	Storage Temperature		-40 to +125	°C
	Mounting Torque (M4)	Recommended Value 1.0-1.4 (10-14)	1.5 (15)	N·m (kgf·cm)
	Mass		23	g

Electrical Characteristics

Symbol	Item	Conditions	Ratings	Unit
I_{DRM}	Repetitive Peak Off-State Current, max.	at V_{DRM} , single phase, half wave, $T_j=125^\circ C$	5	mA
I_{RRM}	Repetitive Peak Reverse Current, max.	at V_{DRM} , single phase, half wave, $T_j=125^\circ C$	5	mA
V_{TM}	Peak On-State Voltage, max.	On-State Current 78A, $T_j=25^\circ C$ Inst. measurement	1.40	V
I_{GT}/V_{GT}	Gate Trigger Current/Voltage, max.	$T_j=25^\circ C, I_T=1A, V_D=6V$	40/3	mA/V
V_{GD}	Non-Trigger Gate, Voltage, min.	$T_j=125^\circ C, V_D=\frac{1}{2}V_{DRM}$	0.2	V
tgt	Turn On Time, max.	$I_T=25A, I_G=100mA, T_j=25^\circ C, V_D=\frac{1}{2}V_{DRM}, dl_G/dt=1A/\mu s$	10	μs
dv/dt	Critical Rate of Rise of Off-State Voltage, min.	$T_j=125^\circ C, V_D=\frac{2}{3}V_{DRM}$, Exponential wave.	100	V/ μs
I_H	Holding Current, typ.	$T_j=25^\circ C$	30	mA
$R_{th(j-c)}$	Thermal Impedance, max.	Junction to case	1.6	°C/W

